

2016 Applied Materials Technical Symposium:

Materials and Process Challenges in Emerging Memory Technologies

Dec. 16, 2016, Shangri-La Tokyo

Time		Title	Presenter
9:00	9:10	Opening	Hitoshi Nakao, Applied Materials
9:10	9:45	New 3D Flash Technologies Offer Both Low Cost and Low Power Solutions	Shigeo Ohshima, Toshiba
9:45	10:10	Selective Removal Technologies for Next Generation Memory and Image Sensors Applications	Vinod Purayath, Applied Materials
10:10	10:35	PVD Technologies for New Memory Applications	Kevin Moraes, Applied Materials
10:35	10:50	Break	
10:50	11:25	Barrier Reliability of Scaled Perpendicular Magnetic Tunnel Junctions for Embedded STT-MRAM	Chando Park, Qualcomm
11:25	11:50	FabVantage Chamber Matching Capability and Case Study on Memory Device	Koyu Asai, Applied Materials
11:50	12:25	Scaling of Floating Gate 3D NAND Flash Memory	Akira Goda, Micron
12:25	12:30	Conclusion	Naoki Oka, Applied Materials
12:30	13:30	Lunch	